



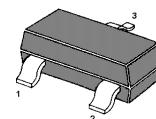
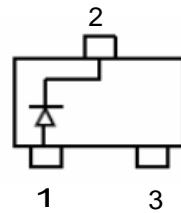
迈拓电子
MAITUO ELECTRONIC

1SS294 SCHOTTKY DIODES

FEATURES

Extremely Fast Switching Speed

Marking : A9



SOT-23

Maximum Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Limits			Unit
Peak Repetitive Peak reverse voltage	V_{RRM}				
Working Peak Reverse Voltage	V_{RWM}	40			V
	V_R				
Forward Continuous Current	I_{FM}	100			mA
Power Dissipation	P_D	200			mW
Storage temperature	T_{STG}	-55-150			°C

Electrical Characteristics @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40			V	$I_R=100\mu\text{A}$
Forward voltage	V_F			0.32	V	$I_F=1\text{mA}$
	V_F			0.5	V	$I_F=10\text{mA}$
	V_F			0.6	V	$I_F=100\text{mA}$
Reverse current	I_R			5	μA	$V_R=40\text{V}$
Diode Capacitance	C_D			25	pF	$V_R=1\text{V}, f=1\text{MHz}$
Reverse Recovery Time	t_{rr}			5	nS	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$



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Typical Characteristics

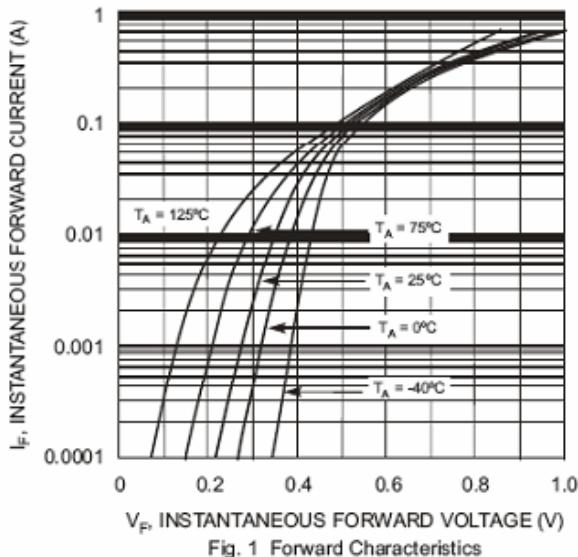


Fig. 1 Forward Characteristics

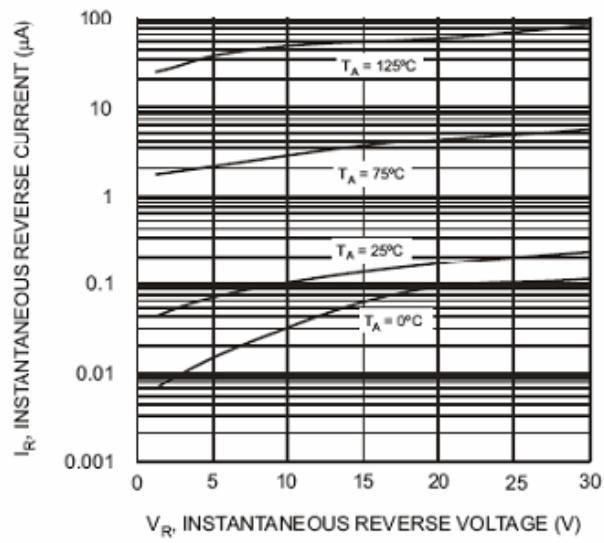


Fig. 2 Typical Reverse Characteristics

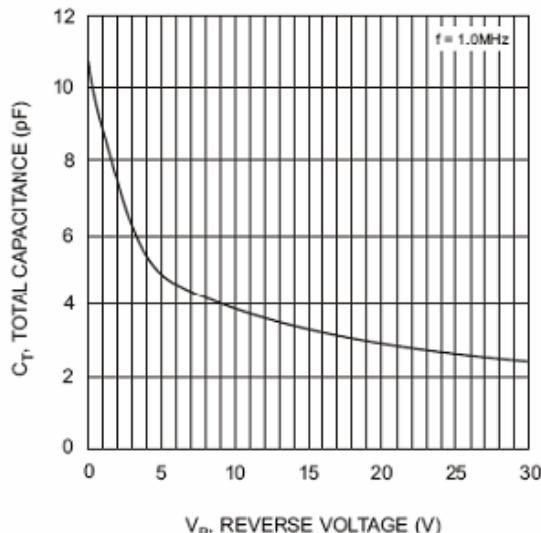


Fig. 3 Typical Capacitance vs. Reverse Voltage

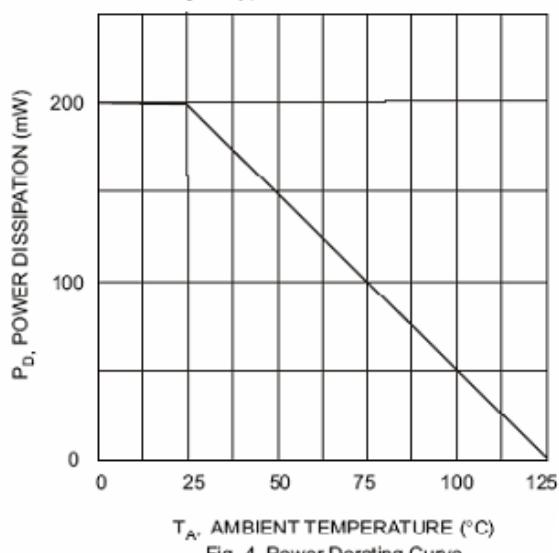


Fig. 4 Power Derating Curve

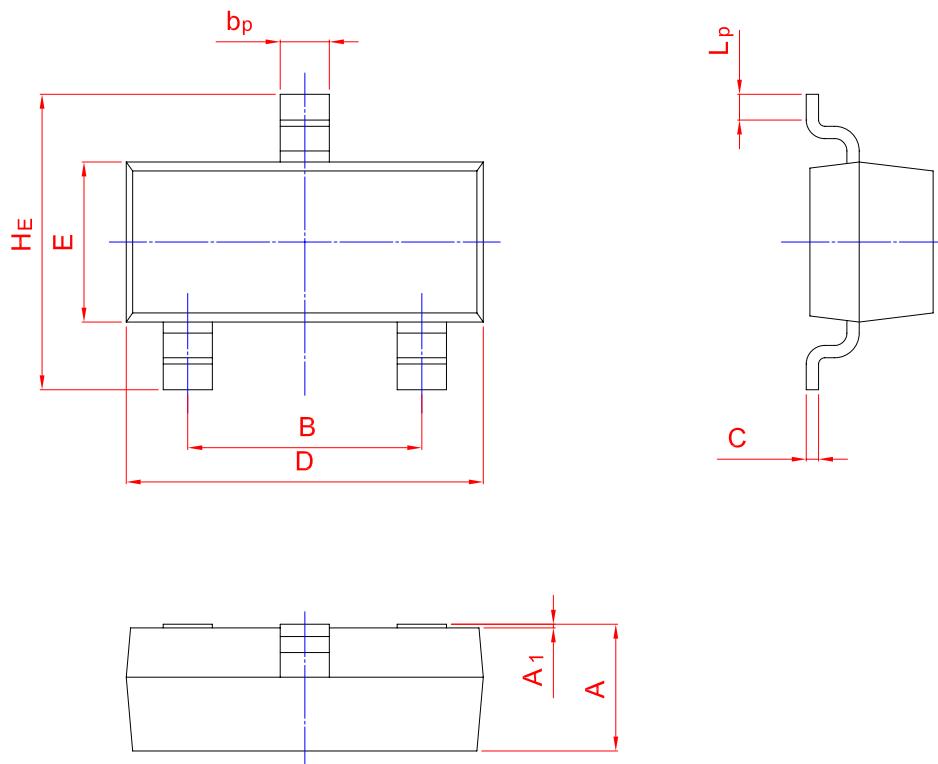


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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20